

Client No. ID12015-US



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor(s):

Kyu-Chan LEE, et al.

Conf. No.

4320

Serial No.:

10/621,165

Examiner:

Not yet assigned

Filing Date:

July 15, 2003

Group Art Unit:

2818

Title:

SEMICONDUCTOR MEMORY DEVICE HAVING AN INTERNAL VOLTAGE

GENERATION CIRCUIT FOR SELECTIVELY GENERATING AN INTERNAL VOLTAGE

ACCORDING TO AN EXTERNAL VOLTAGE LEVEL

Commissioner for Patents P.O. Box 1450

Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

This Information Disclosure Statement is submitted: under 37 CFR 1.97 (b); or (Within three months of filing national application; or date of entry of International application; or before mailing date of first office action on the merits; whichever occurs last) under 37 CFR 1.97 (c) together with either a: Statement under 37 CFR 1.97 (e), or
(Within three months of filing national application; or date of entry of International application; or before mailing date of first office action on the merits; whichever occurs last) under 37 CFR 1.97 (c) together with either a: Statement under 37 CFR 1.97 (e), or
or before mailing date of first office action on the merits; whichever occurs last) under 37 CFR 1.97 (c) together with either a: Statement under 37 CFR 1.97 (e), or
under 37 CFR 1.97 (c) together with either a: Statement under 37 CFR 1.97 (e), or
Statement under 37 CFR 1.97 (e), or
a \$180 fee under 37 CFR 1.17 (p); or
(After mailing of first Office Action, but prior to Notice of Allowance or Final Office Action)
under 37 CFR 1.97 (d) together with:
Statement under 37 CFR 1.97 (e), and
a \$180.00 fee set forth in 37 CFR 1.17 (p).
(Filed after final action or notice of allowance, whichever occurs first, but before payment of
the issue fee)
Applicant(s) submit herewith Form PTO 1449- Information Disclosure Citation together with
copies of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s)
may be material to the examination of this application and for which there may be a duty to disclose in accordance
with 37 CFR 1.56.

It is requested that the information disclosed herein be made of record in this application.

Any deficiency or overpayment should be charged or credited to deposit account number 13-1703. A duplicate copy of this sheet is enclosed.

Customer No. 20575

Respectfully submitted,

MARGER JOHNSON & McCOLLOM, P.C.

Scott A. Schaffer

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I heteby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA

22313-1450

Date: June 23, 2004

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PATENT APPLICATION Docket No. 4591-342 Client No. ID12015-US

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INFORMATION DISCLOSURE CITATION FORM PTO-1449 (Modified)

FOREIGN PATENT DOCUMENTS

Exam <u>Init</u>	Ref	Document Number 11-086544	Publication <u>Date</u> March 30, 1999	<u>Country</u> Japan	<u>Name</u> Yamazaki Kyoji	
		9	OTHER DOCUMEN	<u>TS</u>		
Exam <u>Init</u>	Ref Author, Title, Date, Pertinent Pages, Etc.) English Language Abstract of Japanese Publication No. 11-086544					
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